

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	Package	$I_D$ $T_A = +25^\circ C$
60V	3Ω @ $V_{GS} = 10V$	SOT323	300mA
	4Ω @ $V_{GS} = 5V$		260mA

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc



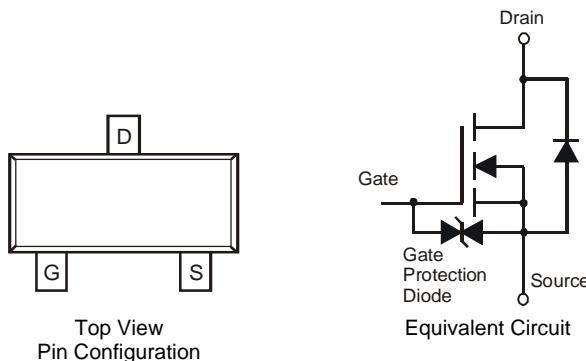
SOT323  
Top View

## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1kV (HBM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN65D8LW-7	SOT323	3000/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



MM3 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: Y = 2011)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017					
Code	Y	Z	A	B	C	D	E					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	300 230	mA
Continuous Drain Current (Note 6) $V_{GS} = 5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	260 210	mA
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)			$I_{DM}$	800	mA
Maximum Body Diode Continuous Current (Note 6)			$I_S$	1	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	$P_D$	300	mW
	(Note 6)		432	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{0JA}$	398	°C/W
	(Note 6)		290	
Thermal Resistance, Junction to Case	(Note 5)	$R_{0JC}$	142	
Operating and Storage Temperature Range	$T_J, T_{STG}$		-55 to +150	°C

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1.0	$\mu\text{A}$	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 5.0$	$\mu\text{A}$	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.2	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	2	3	$\Omega$	$V_{GS} = 10\text{V}, I_D = 0.115\text{A}$
		—	2.5	4	$\Omega$	$V_{GS} = 5\text{V}, I_D = 0.115\text{A}$
Forward Transconductance	$g_{FS}$	80	290	—	mS	$V_{DS} = 10\text{V}, I_D = 0.115\text{A}$
Diode Forward Voltage	$V_{SD}$	-	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	22.0	—	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	3.2	—		
Reverse Transfer Capacitance	$C_{rss}$	—	2.0	—		
Gate Resistance	$R_G$	—	79.9	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge $V_{GS} = 10\text{V}$	$Q_g$	—	0.87	—	nC	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 150\text{mA}$
Total Gate Charge $V_{GS} = 4.5\text{V}$	$Q_g$	—	0.43	—		
Gate-Source Charge	$Q_{gs}$	—	0.11	—		
Gate-Drain Charge	$Q_{gd}$	—	0.11	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.7	—	nS	$V_{DD} = 30\text{V}, I_D = 0.115\text{A}, V_{GEN} = 10\text{V}, R_{GEN} = 25\Omega$
Turn-On Rise Time	$t_r$	—	2.8	—		
Turn-Off Delay Time	$t_{D(off)}$	—	12.6	—		
Turn-Off Fall Time	$t_f$	—	7.3	—		

Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

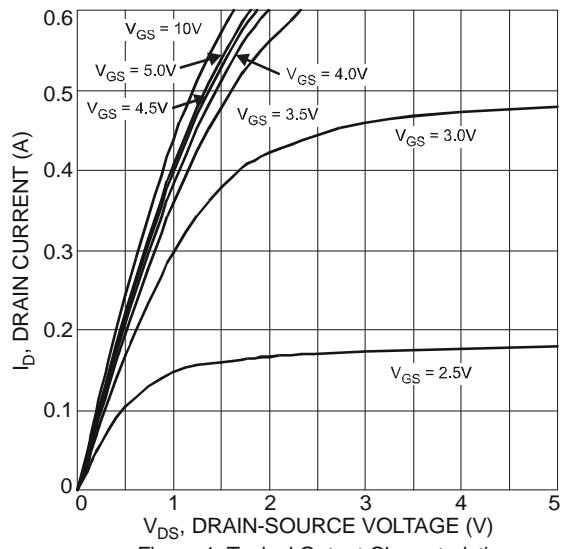


Figure 1 Typical Output Characteristic

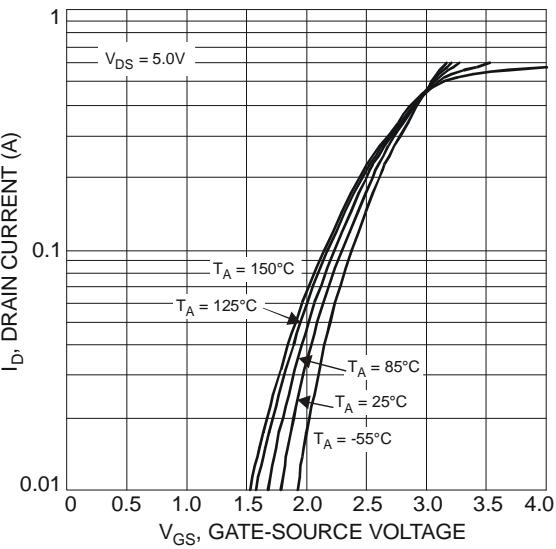


Figure 2 Typical Transfer Characteristics

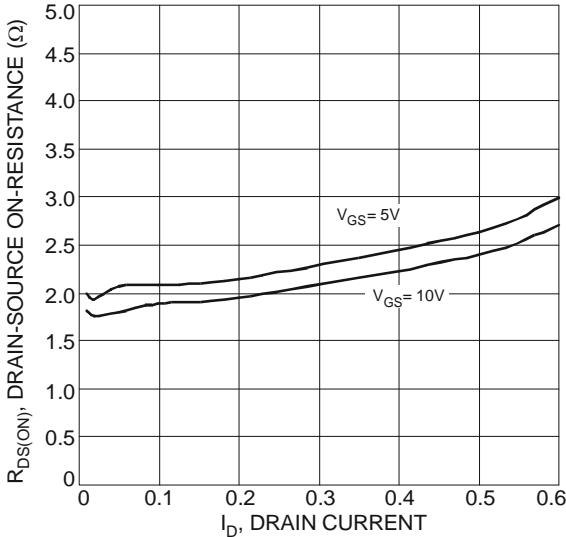


Figure 3 Typical On-Resistance vs.  
Drain Current and Temperature

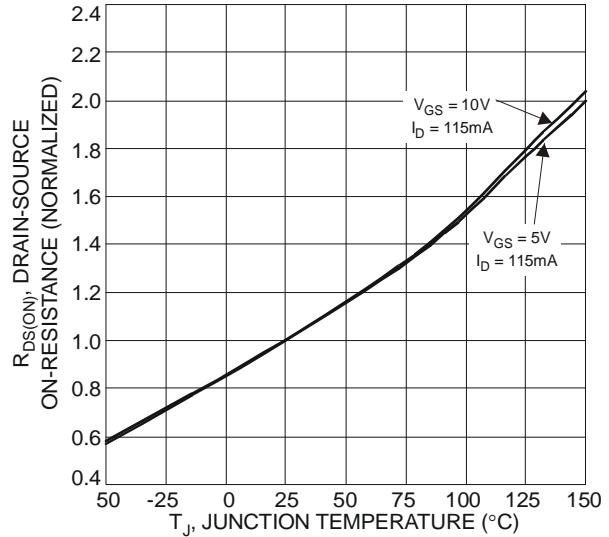


Figure 4 On-Resistance Variation with Temperature

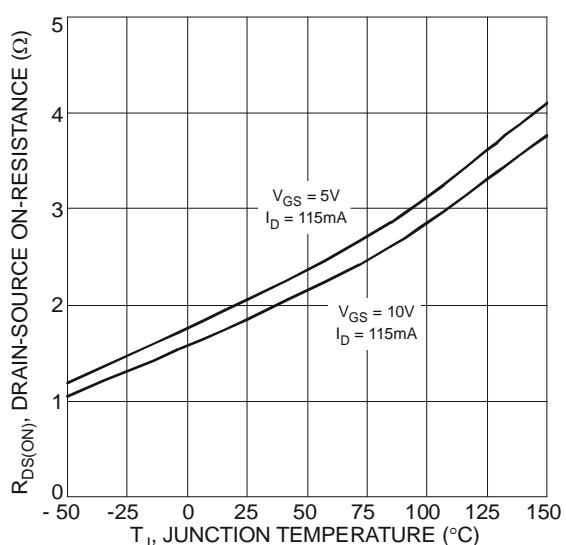


Figure 5 On-Resistance Variation with Temperature

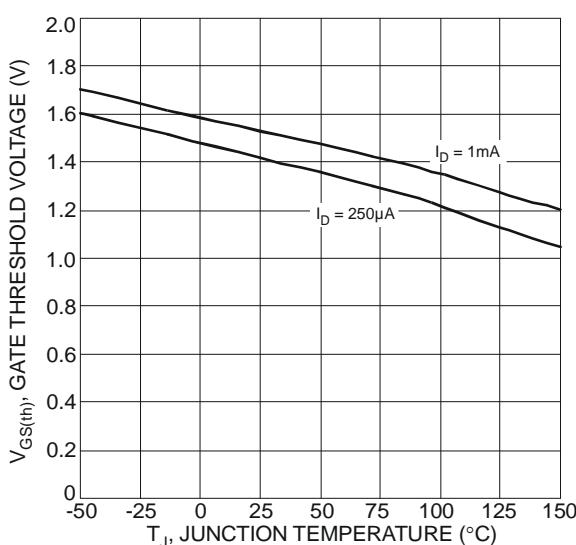


Figure 6 Gate Threshold Variation vs. Ambient Temperature

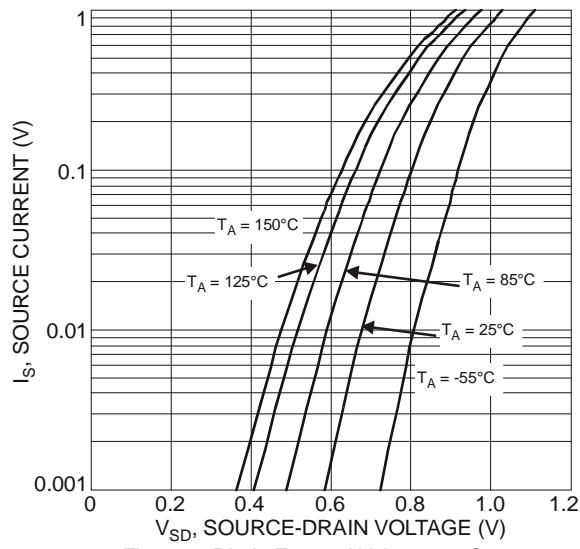


Figure 7 Diode Forward Voltage vs. Current

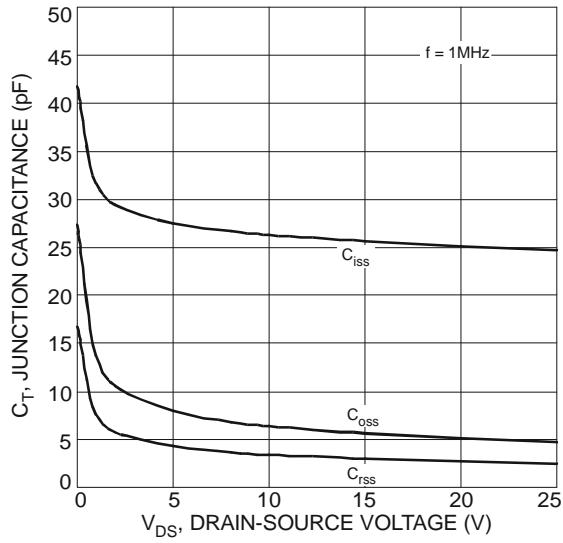


Figure 9 Typical Junction Capacitance

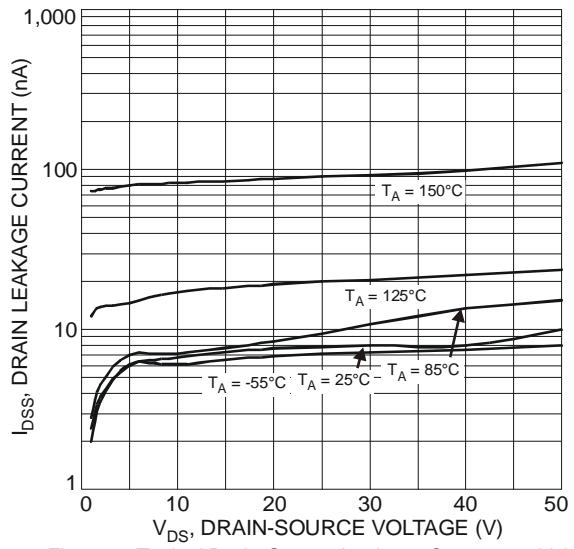


Figure 8 Typical Drain-Source Leakage Current vs. Voltage

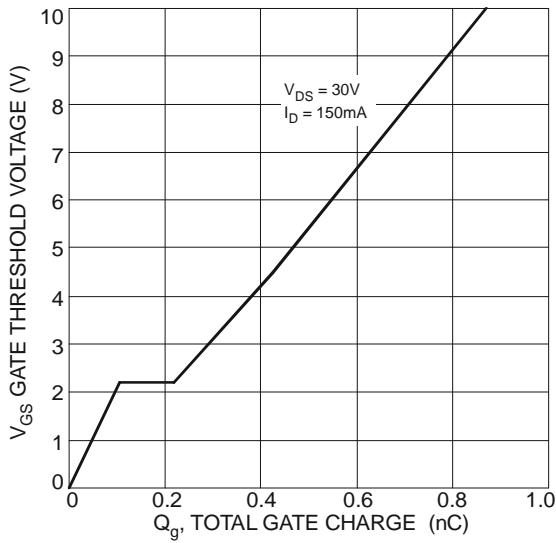
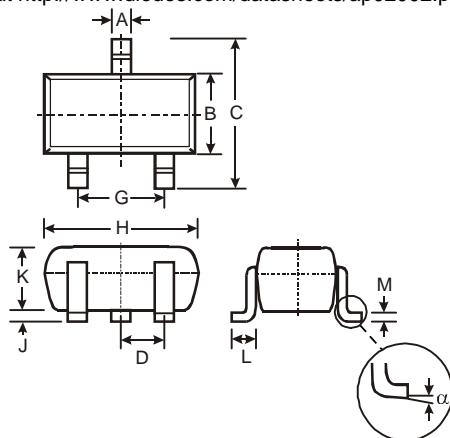


Figure 10 Gate Charge

## Package Outline Dimensions

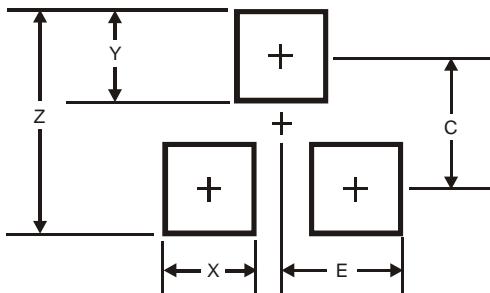
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
$\alpha$	0°	8°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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